Slow Conductance Relaxation in Graphene–Ferroelectric Field-Effect Transistors

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ABSTRACT: Tuning graphene conduction states with the remnant polarization of ferroelectric oxides holds much promise for a range of low-power transistor and memory applications. However, understanding how the ferroelectric polarization affects the electronic properties of graphene remains challenging because of a variety of intricate and dynamic screening processes that complicate the interaction. Here, we report on a range of slow electrical conductance relaxation behavior in graphene–ferroelectric field-effect transistors with the extreme case leading to the convergence of two polarization-induced states. Piezoresponse force microscopy through the graphene channel reveals that the ferroelectric polarization remains essentially unchanged during this conductance relaxation. When measured in vacuum, the conductance relaxation is significantly reduced, suggesting equilibration from the ambient atmosphere that can cause charge transfer to and from graphene to be the origin of the slow relaxation.

INTRODUCTION

Since its discovery\textsuperscript{1,2} and the subsequent development of large-area growth techniques,\textsuperscript{3–5} graphene has been considered for an extensive range of applications including chemical sensing,\textsuperscript{6–9} flexible and transparent electrodes,\textsuperscript{10,11} field-effect transistors (FETs),\textsuperscript{12–14} and information storage devices.\textsuperscript{15} This diversity of applications stems from its unique electronic structure in conjunction with robust mechanical and chemical properties all encompassed in an atomically thin material. With respect to FET and memory applications, interfacing graphene with ferroelectric materials has been proposed to provide several benefits.\textsuperscript{16–18} For example, ferroelectric gate oxides in graphene FETs can not only reduce the operating voltage as a result of the high dielectric constant\textsuperscript{19} but also provide additional means of manipulating the Fermi level position with polarization direction.\textsuperscript{20,21} For a structure consisting of graphene on top of a ferroelectric oxide substrate, UP polarization (i.e., polarization pointing toward the graphene) should, in theory, cause graphene to become more n-type, while DOWN polarization (i.e., polarization pointing away from the graphene) should induce more p-type behavior. These two states can be accessed simply with a small applied gate voltage ($V_g$) driving reversal of the polarization, opening the door to memory applications. Furthermore, patterning polarization domains with established methods allows spatially modulated doping of graphene.\textsuperscript{25}

The coupling between the ferroelectric polarization direction and graphene Fermi level position is, however, complicated, as evidenced by several reports of the Dirac point (DP) shifting in both the expected and the unexpected directions in response to polarization switching in atmospheric conditions.\textsuperscript{18–20,22,26} Here and throughout, DP shift refers to the shift in $V_g$ at which the DP appears. Additionally, even when the DP shift is in the expected direction, the magnitude of the shift is significantly smaller than expected for a complete charge compensation of the ferroelectric polarization.\textsuperscript{22} The polarization can be screened by charges from complicating factors at the interface such as adsorbed H$_2$O,\textsuperscript{26} ferroelectric surface reconstructions,\textsuperscript{26} charged defects, and impurities.\textsuperscript{25} Further complications arise when one considers how the measurements are interpreted. One common approach to switch ferroelectric polarization in graphene–ferroelectric FETs is by sweeping $V_g$ at a range above the coercive voltage. A shift in the conductance minimum corresponding to the DP can then be used to quantify changes in the Fermi level of the graphene. However, the underlying picture of the ferroelectric switching process, when analyzed in this manner, is complicated because of a wide range of factors, including adsorption–desorption of ambient molecules, substrate charging, and other factors that can all cause a shift in the $V_g$ at which the DP appears and/or reduce the transconductance around the DP in graphene FETs. Incorporating an additional effect from polarization switching further complicates the interpretation of such measurements.

Additionally, there has been little direct experimental evidence for actual polarization switching under the graphene channel. Given that the intrinsic carrier concentration of graphene is an order of magnitude smaller than that required to completely compensate the remnant polarization of the ferroelectric oxide, the presence of a depolarization field and...
thus the possible formation of antiparallel domains cannot be ruled out. Knowing the polarization landscape is then critical to interpreting electrical measurements because nonuniform doping of the graphene channel can cause complications such as a change in $V_{th}$ where the DP appears and reduced transconductance. Hence, separating out ferroelectric polarization effects from other extrinsic factors that influence graphene conductivity and doping level upon switching of polarization remains a critical task. Direct measurements of the polarization under the graphene has recently been performed using piezoresponse force microscopy (PFM). However, the limited length scale that has been examined (∼1 μm$^2$) makes it difficult to infer the polarization over the entire channel region of most graphene–ferroelectric FETs (which have areas of several to tens of square micrometers). PFM has also been used to examine polarization switching in BaTiO$_3$ using carbon nanotubes (CNTs). In that study, the switched regions had widths much larger than those of CNTs and were imaged after the removal of CNTs, emphasizing the importance of paying careful attention to extrinsic effects including compensation of the ferroelectric polarization by adsorbates from the ambient surrounding. Here, we study graphene FETs with PbZr$_{0.2}$Ti$_{0.8}$O$_3$ (PZT) as the gate oxide and observe a slow conductance relaxation of varying degree over several hours. In some cases, this slow relaxation can lead to a complete convergence of the two states initially set by polarization switching. On the basis of PFM measurements over the entire graphene channel area, we conclude that this slow equilibration process is not caused by the relaxation of the ferroelectric polarization. Furthermore, we observe a significant suppression of this relaxation phenomenon in vacuum, indicating equilibration between the ambient molecules and graphene is responsible for the observed effect.

**METHODS**

Graphene was grown using an established chemical vapor deposition method on Cu foil (99.999% Puratronic, Alfa Aesar). Raman spectra of the graphene transferred to Si/SiO$_2$ do not exhibit detectable D-band, as shown in the Supporting Information (Figure S1). The one-touch transfer method described in ref 22 was used to transfer the graphene onto a 150 nm PZT film grown by pulsed laser deposition on a SrTiO$_3$ (001) substrate with a 20 nm SrRuO$_3$ serving as the bottom electrode. Before graphene was transferred to the PZT substrate, the surface was characterized with PFM. The surface scans revealed a smooth sample surface (∼150 pm roughness) as well as a uniform polarization orientation, as shown in the topography and phase images in panels A and B of Figure S2, respectively. Additional measurements revealed that the as-grown polarization state of the PZT was in the UP direction, as indicated in Figure S2D. Before graphene transfer, the PZT film and substrate were annealed at 300 °C for 30 min under 500 sccm O$_2$ flow to remove residual surface contaminants. Upon transfer of the graphene, electrical contacts were defined using standard photolithography techniques. The device structure has been previously reported and is schematically shown in Figure 1A. First, 100 nm SiO$_2$ islands were deposited by electron-beam evaporation, which was followed by 3 nm/25 nm Ti/Pd layers. An additional 25 nm Pd layer was deposited to contact the graphene. We found the SiO$_2$ islands necessary to reduce leakage current between the Pd and SrRuO$_3$ contacts as previously reported. A channel width of 5 μm and length of 3 μm were defined by standard photolithography using AZ 5214E photoresist and O$_2$ plasma etching. Atomic force microscopy (AFM) topography measurements revealed the presence of a residue layer after device fabrication. This thin layer was removed by scanning the channel with an AFM tip operating in the contact mode with a 100 nN scanning force. Representative channel topography images as well as $V_s$ sweeps before and after AFM cleaning are shown in the Supporting Information (Figure S3). Initial poling of the devices was carried out by cycling 7 V, 1 s pulses of alternating polarity for a total of 3–5 cycles. The time trace of this initial poling process is shown in Figure 1B for a device that required three sequential cycles of switching. It was found that this initial poling procedure led to more reproducible results and maximized the graphene DP shift with ferroelectric polarization switching. Electrical measurements were performed using an Agilent 4156C semiconductor parameter analyzer. Gate voltage pulses were applied using a BK Precision 4052 arbitrary waveform generator. PFM measurements were performed using an Asylum Cypher AFM running in dual AC resonance tracking (DART) mode with a scanning force of 10 nN and tip voltage <1 V. Vacuum measurements were carried out in a home-built vacuum probe station operating at a pressure of 10$^{-6}$ Torr.

**RESULTS AND DISCUSSION**

The graphene FETs studied herein are schematically shown in Figure 1A. Similar devices have been used to examine how the polarization of ferroelectric oxides can be switched by graphene and how it can, in turn, alter the carrier type and density in graphene. This coupling of the ferroelectric polarization direction with the graphene conduction is illustrated in Figure 1B which plots the time trace of the graphene drain current ($I_d$)
under a small bias of 50 mV during the initial cycling procedure (switching by sweeping $V_g$ above the coercive voltage, verified by the DP shift and the peaks in the gate current at $V_g \approx \pm 2.5$ V, is shown in Figure S4). The orange time traces correspond to the graphene conductance state after the application of a square $V_g$ pulse of 1 s duration and $+7$ V magnitude to the bottom contact, which should cause the polarization of the PZT to be poled UP. The blue time traces refer to the graphene conductance state after application of a square $V_g$ pulse of 1 s duration and $-7$ V magnitude, switching the system to the DOWN polarization state. Within $\sim 250$ s after applying each switching pulse, the device appears to have mostly equilibrated, indicating two stable states presumably induced by the two polarization states of the PZT. The expected changes in the $I_d-V_g$ characteristics are similar to what is shown in Figure 1C. Upon switching the polarization DOWN, the graphene becomes significantly more p-type, causing the DP to appear beyond the $V_g$ window of the measurement. When the polarization is switched UP, the graphene becomes n-type with the DP appearing at $V_g \approx -0.5$ V, corresponding to an estimated electron density of $5.5 \times 10^{12}$ cm$^{-2}$. Although the polarization of PZT can be switched with smaller and shorter $V_g$ pulses in most devices, $\pm 7$ V pulses of 1 s duration were used here (unless noted otherwise) to ensure as complete of a switching of the polarization as possible.

An important aspect of graphene–ferroelectric FETs is the long-term stability of the ferroelectrically coupled graphene conductance states. Figure 1C suggests that the two polarization directions of the PZT lead to two stable p and n regimes as determined by the sign of the transconductance at $V_g = 0$ V. To explore the stability of these states, we monitored several devices over a longer time period, and Figure 2 shows the range of responses observed. Figure 2A,B provides an example when these two states are relatively stable. In Figure 2A, $V_g$ dependence for both the UP and DOWN states immediately and 24 h after applying the switching pulses are shown. Multiple gate sweeps were performed over the course of this 24 h period, and $I_d$ at $V_g = 0$ V is plotted as a function of time in Figure 2B. While there is only a small change for the DOWN polarization state, the UP state exhibits a significant relaxation within $\sim 7$ h after switching. More extreme relaxation can be observed in some devices, as shown in Figure 2C, where the $I_d-V_g$ characteristics converge with identical DP locations at $\sim 0.7$ V. The corresponding time evolution of $I_d$ at $V_g = 0$ V is shown in Figure 2D. That is, the two ferroelectric polarization-induced states of graphene eventually equilibrate to what appears to be the same state.

The slow relaxation behaviors for several devices are compared in Figure 2E by plotting the amount that $I_d$ has relaxed over 24 h ($I_r$) versus the initial change in current due to ferroelectric polarization switching for several different devices. Open symbols indicate devices that have undergone channel cleaning with the AFM tip, and solid symbols are those that have not. Error values along each axis were estimated as the square root of the sum of the squares of the two current error values, each of which were calculated as described in the caption for Figure 1C.
polarization DOWN leads to a wide range of behavior from no change to convergence with the UP polarization case. One possible explanation is that the conduction state before any polarization switching events is the stable state for the UP polarization. The substrate was initially poled UP, and the surface was completely compensated before graphene transfer (Figure S2). Hence, it is possible that when the polarization is switched UP, the relaxation involves only extrinsic factors such as rearrangement of adsorbed molecules, whereas relaxation from switching polarization DOWN may involve an additional and larger energy barrier process of reversing the ferroelectric polarization direction. It has been shown that a ferroelectric thin film with an uncompensated surface can lead to domain wall formation and promotion of back-switching into a polydomain state to minimize depolarization effects. Then, a varying degree of polydomain states, especially for the DOWN polarization case where it may be more likely to result in an uncompensated surface, can lead to a varying degree of slow relaxation. Alternatively, the range of behavior may be entirely due to dynamic screening processes arising from equilibration of charged or polar adsorbates, which can be sensitive to variations in the surroundings as well as to the history of the sample. Whether the long time-scale relaxation and its varying degree from device to device arise from an adsorbate-induced screening process, actual changes in the ferroelectric polarization orientation, or a combination thereof remains unclear and are mere speculation without direct experimental evidence. In this regard, PFM imaging of the polarization domain landscape underneath the graphene channel to correlate to the observed electrical response can provide much needed insights. Currently, direct evidence of whether there is a complete ferroelectric polarization switching under the entire graphene channel region, much less how the polarization might evolve over time, is lacking. To probe the potential role of the underlying ferroelectric domain structure directly, we performed PFM measurements through the single-layer graphene over the entire channel area of our FETs following different switching operations, as shown in Figure 3. Details of PFM measurements carried out in DART mode are discussed in the Supporting Information with additional data shown in Figure S6. Specifically, we focused on devices that exhibited the extreme relaxation behavior where there is a convergence of the UP and DOWN states upon relaxation, as exemplified in Figure 2C,D. As shown in Figure 3A,C, distinct differences in the phase between UP and DOWN polarization can be seen immediately after switching. For the DOWN state, there are some small UP polarization domains that either did not fully switch or quickly relaxed after removing the switching voltage. The UP state appears to be more uniform. Some of the UP domains observed in the DOWN switched case may possibly be due to varying interfacial conditions across the channel that may locally increase the coercive voltage in these regions or cause domain growth to become pinned.

What is striking from the PFM images is that 24 h after polarization switching, there is no significant change to the ferroelectric polarization domain landscape as revealed by panels B and D in Figure 3 for the DOWN and UP states, respectively. The unswitched regions in the DOWN case do grow slightly, but this small change is unlikely to account for the conductance relaxation of both UP and DOWN cases to end up with the same carrier density. Furthermore, for the UP polarization case (Figure 3C,D), there is no discernible difference between PFM images taken immediately and 24 h after the polarization switching; however, there is still a large conductance relaxation. Hence, extrinsic factors (charges or molecules at the interface between graphene and PZT and/or the interaction with the surrounding atmosphere) dominate the observed slow conductance relaxation.

Although we have chosen ±7 V, 1 s pulses based on PFM results to ensure complete (or at least maximum) switching of the ferroelectric polarization, the magnitude of this $V_p$ pulse is well above the expected coercive voltage of ~2–3 V observed in switching by sweeping $V_g$ for our device geometry. Then, whether or not the slow conductance relaxation is an artifact of the large applied potential needs to be considered carefully. To this end, we have examined a range of pulse widths and amplitudes, as shown in Figure 4A. The difference between $I_{UP}$ and $I_{DOWN}$ are plotted as a function of pulse width and height. Before each switching $V_g$ pulse, the device was reset with a corresponding positive or negative $V_g$ pulse and allowed to relax over 250 s to ensure that the initial state was oppositely poled. Similar results were seen without this reset pulse with the exception of overlapping data points in the low-voltage regime where no apparent switching of the ferroelectric polarization occurs. Pulse amplitude of ~3 V does not appear to have much effect on the observed electrical response.
to cause sufficient change in the conductance of graphene (and therefore presumably the polarization direction of the underlying PZT) even at 1 s pulse width. With +3 V pulse, 1 s appears to be the minimum duration needed to cause conductance change in graphene consistent with full polarization switch. For 5 V pulse magnitude, the minimum pulse widths needed appears to be $\sim 10 \mu$s and $\sim$ 1 ms to achieve magnitude of change in conductance consistent with fully switching the polarization UP and DOWN, respectively.

Using conditions close to the above minimum $V_g$ pulse magnitude and duration requirement, slow conductance relaxation was examined by electrical and PFM measurements. Figure 4B,C shows that using $-5$ V, 100 ms and $+5$ V, 1 ms $V_g$ pulses leads to a response that is essentially identical to that of the $\pm 7$ V, 1 s $V_g$ pulse cases. That is, the same conductance relaxation within 24 h of switching occurs without the corresponding changes in the actual polarization of the PZT. The relaxation observed in the DOWN state shows a small growth of the UP domains similar to the relaxation behavior observed in the $-7$ V, 1 s case discussed above. In the case of switching the polarization UP with $+5$ V, 1 ms pulse, initial PFM shows many small $\sim 200$ nm diameter circular DOWN polarized domains, indicating that this combination of amplitude and duration of $V_g$ pulse is actually slightly insufficient to cause complete switching. However, there is already a maximum change electrically under these conditions. The small DOWN polarized domains disappear over 24 h, leading to a more homogeneously UP poled PZT. One would then expect the graphene to slowly become more n-type, completely opposite to the observed shifting to p-type. Hence, we conclude that the slow conductance relaxation is not an artifact of the large $V_g$ pulse amplitude and that it occurs while the polarization of the underlying PZT remains essentially unaltered.

Because the observed slow conductance relaxation is not correlated to the underlying polarization of the PZT, its origin must arise from graphene interacting with the ambient surrounding and/or with the interfacial states and molecules in between graphene and PZT. Indeed, a previous report has suggested that H$_2$O and its dissociated ions at the interface between a few-layer graphene and PZT can cause a slow conductance relaxation. The substrate was also maintained at room temperature throughout to minimize altering the graphene–ferroelectric interface. Figure 5A shows how $V_g$ dependence of $I_d$ evolves after placing the devices in vacuum. Graphene becomes less p-type, presumably due to the removal of adsorbed molecules. After allowing the devices to equilibrate in vacuum for 24 h, ferroelectric polarization switching via $\pm 7$ V, 1 s pulses was repeated as in the air ambient conditions. The relaxation observed in our case is likely to arise from interactions with ambient molecules in air. Once the sample was removed from vacuum and placed in air, the slow conductance relaxation returned. PFM images taken in air following polarization switching in vacuum show that the polarization had indeed switched and remain switched while in vacuum (Figure 5C). These observations point to the equilibration of adsorbates on graphene upon polarization switching of the underlying ferroelectric gate dielectric to be the origin of the slow conductance relaxation.

The above observations suggest that the switching of the underlying ferroelectric polarization leads to Fermi level position change in graphene that (partially) compensates the polarization change initially, but the subsequent interaction with the surrounding environment leads to charge transfer and changes in screening by adsorbates on the graphene. This equilibration with the ambient surroundings in turn causes the observed conductance relaxation. When this equilibration occurs, the polarization of the ferroelectric remains essentially unchanged. Then the interactions with the ambient adsorbates must also compensate the ferroelectric polarization that graphene used to. It should be noted that a slow relaxation was not observed for graphene FETs with a ferroelectric top gate dielectric, but the thick 200 nm ferroelectric polymer film may be isolating graphene from the ambient atmosphere. Additionally, a significantly smaller remnant polarization of ferroelectric polymers may lead to less of a magnitude and driving force for relaxation induced by adsorbates. The combined effects of exposure to the surrounding environment and high polarization fields may make our devices more susceptible to a range of charge compensation mechanisms.

Previously proposed mechanisms that can affect polarization compensation include O-derived defects on graphene interact-
ing with the substrate surface,\textsuperscript{26} dynamic dissociation–recombination of H\textsubscript{2}O chemisorbed on ferroelectric surface,\textsuperscript{18} dipole orientation of trapped H\textsubscript{2}O molecules,\textsuperscript{24} and trapped surface charges.\textsuperscript{25} However, all of these mechanisms involve effects arising at the interface between graphene and the ferroelectric oxide and therefore are not likely to account for the differences in air versus under vacuum conditions observed here and the polarization of the underlying substrate remaining unchanged through the slow conductance relaxation. Following Levesque et al., we then consider the H\textsubscript{2}O/O\textsubscript{2} redox process on the surface of graphene facilitated by the polar substrate surface similar to what has been considered for graphene FETs on SiO\textsubscript{2}.\textsuperscript{41}

\[
O_2(\text{aq}) + 4H^+ + 4e^- (\text{graphene}) \rightarrow 2H_2O
\]  

(1)

Equilibration with the H\textsubscript{2}O/O\textsubscript{2} redox couple results in charge transfer to and from the graphene depending on the initial Fermi level position of the graphene. When the ferroelectric polarization of the underlying substrate is switched, it causes a change in carrier density in graphene. This change in turn drives adsorption of H\textsubscript{2}O and O\textsubscript{2} molecules from the surroundings which will then lead to charge transfer to and from graphene through the redox reaction 1. The time scale of this process is several hours,\textsuperscript{41} consistent with the slow kinetics we observe. Polar molecules and/or charged species can also contribute to compensating the ferroelectric polarization, resulting in stable ferroelectric domain landscape. We note that this redox reaction could, at least in part, account for the observed change in carrier density in graphene being smaller than that needed to fully compensate polarization switch in the ferroelectric oxide. Under vacuum conditions, there is less H\textsubscript{2}O and O\textsubscript{2} available from the atmosphere, changing the equilibrium state and therefore causing larger Fermi level shift in graphene upon polarization switching and eliminating or reducing slow conductance relaxation.

\section*{CONCLUSIONS}

We have shown that there is a conductance relaxation process that occurs over several hours after polarization switching in graphene FETs utilizing PZT as the ferroelectric gate oxide. The magnitude of the conductance relaxation varies from device to device, but there is consistently a significant relaxation upon switching the polarization UP, whereas the relaxation upon switching DOWN can vary from essentially no change to complete change that leads to the convergence of the two polarization-induced conduction states into what appears to be the same state. Direct PFM imaging of the polarization domain landscape underneath the entire graphene channel has revealed that the polarization of the underlying PZT remains essentially unchanged during this electrical relaxation process. Measurements carried out in vacuum indicate that the slow conductance relaxation is associated with equilibration with adsorbates from the ambient surroundings. We suggest the H\textsubscript{2}O/O\textsubscript{2} redox couple that has been shown to exhibit similar slow equilibration with graphene on Si/SiO\textsubscript{2} substrate as a possible origin of the conductance relaxation upon ferroelectric polarization switching.

\section*{ASSOCIATED CONTENT}

\section*{Supporting Information}

The Supporting Information is available free of charge on the ACS Publications website at DOI: 10.1021/acs.jpcc.7b00753.

Extended description of PFM measurements; Raman spectrum of graphene utilized in this study (Figure S1); PFM data of the substrate before device fabrication and after tip bias-induced polarization switching (Figure S2); AFM images and electrical data before and after cleaning graphene with an AFM tip (Figure S3); drain and gate current dependence on gate voltage upon sweeping above the coercive voltage (Figure S4); electrical data demonstrating calculation of current change upon switching and relaxation (Figure S5); representative extended data obtained by DART-PFM measurements (Figure S6); evolution of gate dependence in vacuum over the course of a week (Figure S7) (PDF)

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\section*{Notes}

The authors declare no competing financial interest.

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